

# Grazing incidence X-rays diffraction: a powerful tool for 2D materials studies

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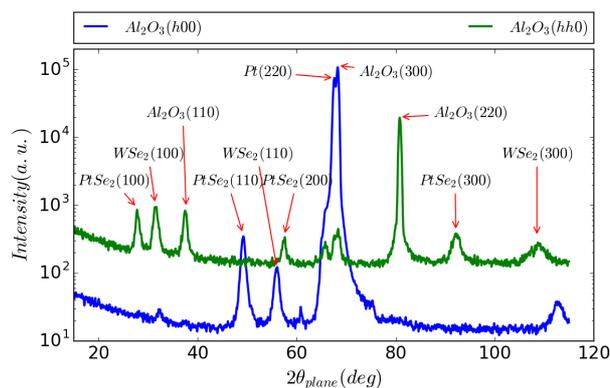
Layered, transition metal dichalcogenides (TMD), exhibit fascinating properties when the thickness is reduced to atomic size. For example, a transition from an indirect to a direct band gap can appear making them very attractive in electronics and optoelectronics [1]. The synthesis of high quality 2D TMD on large area is required to meet the microelectronics standards. For this purpose, we developed Se-based 2D TMDs (MoSe<sub>2</sub>, WSe<sub>2</sub>, PtSe<sub>2</sub> etc.) grown by molecular beam epitaxy [2] on various substrates. Determining the crystalline orientations, strains, and grain sizes is of great importance to understand properties and to improve the growth. The in-plane grazing incidence x-rays diffraction technique [3] is well suited for the structural analysis of these layered materials on large surface. Our measurements were performed using a laboratory set-up equipped with a rotating anode (45kV @ 200mA). Two in-plane scans types were performed: i) reciprocal radial scans along directions of the substrate in order to determine in-plane lattice parameters, strains and domain sizes. ii) Azimuthal scans performed at Bragg angles found in the radial scans in order to investigate in-plane orientation and mosaic of the 2D layers with respect to the substrate. An example of such measurements is shown on the figures below for a multilayer WSe<sub>2</sub>/PtSe<sub>2</sub>

grown on a Pt(111)/sapphire(0001). The results for the various TMD/substrates couples will be discussed, showing a large variety of epitaxial growths.

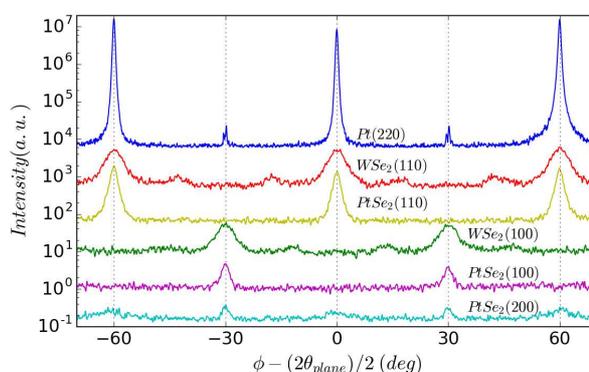
## References

- [1] Wang Q. H. et al. Nature Nanotech, 7 (2012) 699
- [2] Dau M.T. et al., Appl. Phys. Lett., 110 (2017) 011909
- [3] Gu X. et al., ChemSusChem, 7 (2014) 416

## Figures



**Figure 1:** in-plane radial scans along  $\langle h00 \rangle$  and  $\langle hh0 \rangle$  sapphire substrate directions



**Figure 2:** in-plane azimuthal scans for various Bragg reflections of the substrate and of the over-layers